

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 (currently amended). A quasi-vertical semiconductor component, comprising:

a surface;

a semiconductor substrate;

a well;

at least two inner cells disposed in said well ~~and having a substantially similar operating point, thereby compensating for differences between said inner cells;~~

a buried layer disposed between said well and said semiconductor substrate; ~~and~~

a sinker zone disposed outside a region of said inner cells and defining a sinker voltage, said sinker zone connecting

said buried layer to said surface of the semiconductor component; and

said inner cells having substantially similar values for forward currents and reverse currents being independent of a positional relationship to said sinker zone by varying a given width of said inner cells and/or a given radius of curvature of said inner cells and/or a spacing between said inner cells in dependence on the sinker voltage.

2 (canceled).

3 (currently amended). The semiconductor component according to claim 1 2, wherein said inner cells have body zones with a given width and a given radius of curvature, and that at least one of said given width of said body zones, said given radius of curvature of said body zones, and a spacing between ~~grid configuration of~~ said body zones of said inner cells is varied.

4 (currently amended). The semiconductor component according to claim 3, wherein said body zones are ~~one of~~ wider ~~and~~ and/or have a larger radius of curvature in a vicinity of said sinker zone than at a distance from said sinker zone.

5 (currently amended). The semiconductor component according to claim 3, wherein said spacing between ~~grid configuration of~~ said inner cells has a larger spacing distance at a distance from said sinker zone than in a vicinity of said sinker zone.

6 (currently amended). The semiconductor component according to claim 1 ~~2~~, further comprising doped regions disposed in said well, a variation of at least one of said given width, said given radius of curvature and said spacing between ~~grid configuration of~~ said inner cells ~~zones~~ is effected by said doped regions.

7 (original). The semiconductor component according to claim 6, wherein said doped regions are introduced by high-energy ion implantation.

8 (original). The semiconductor component according to claim 7, wherein said doped regions lie between said well and said body zone of said inner cells.

9 (original). The semiconductor component according to claim 1, wherein said well has an edge region and said sinker zone is disposed at said edge region.